



PTO/SB/08 Equivalent

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Multiple sheets used when necessary)	Application No.	10/634,212
	Filing Date	August 5, 2003
	First Named Inventor	Karen Signorini
	Art Unit	2813
SHEET 1 OF 3	Examiner	Jennifer M. Dolan
	Attorney Docket No.	MICRON.249C1DV1

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
JMD	1	3,553,660	01/05/1971	Wolf	
JMD	2	3,623,032	11/23/1971	Schapira	
JMD	3	3,623,035	11/23/1971	Kobayashi et al.	
JMD	4	3,816,909	06/18/1974	Maeda et al.	
JMD	5	3,947,831	03/30/1976	Kobayashi et al.	
JMD	6	4,044,330	08/23/1977	Johnson et al.	
JMD	7	4,060,794	11/29/1977	Feldman et al.	
JMD	8	4,065,742	12/27/1977	Kendall et al.	
JMD	9	4,158,891	06/19/1979	Fisher	
JMD	10	4,455,626	06/19/1984	Lutes	
JMD	11	4,666,554	05/19/1987	De Wilde et al.	
JMD	12	4,731,757	03/15/1988	Daughton et al.	
JMD	13	4,780,848	10/25/1988	Daughton et al.	
JMD	14	4,801,883	01/31/1989	Muller et al.	
JMD	15	4,849,695	07/18/1989	Muller et al.	
JMD	16	4,897,288	01/30/1990	Jenson	
JMD	17	4,918,655	04/17/1990	Daughton	
JMD	18	4,945,397	07/31/1990	Schuetz	
JMD	19	5,039,655	08/13/1991	Pisharody	
JMD	20	5,060,193	10/22/1991	Daughton et al.	
JMD	21	5,064,499	11/12/1991	Fryer	
JMD	22	5,140,549	08/18/1992	Fryer	
JMD	23	5,424,236	06/13/1995	Daughton et al.	
JMD	24	5,496,759	03/05/1996	Yue et al.	
JMD	25	5,547,599	08/20/1995	Wolfrey et al.	
JMD	26	5,569,617	10/29/1996	Yeh et al.	
JMD	27	5,756,366	05/26/1998	Berg et al.	
JMD	28	5,587,943	12/24/1996	Torok et al.	
JMD	29	5,650,958	07/22/1997	Gallagher et al.	

Examiner Signature <i>Jennifer M. Dolan</i>	Date Considered <i>3/20/05</i>
*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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## U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
JMD	30	5,701,222	12/23/1997	Gill et al.	
JMD	31	5,726,498	03/10/1998	Licata et al.	
JMD	32	5,741,435	04/21/1998	Beetz, Jr. et al.	
JMD	33	5,756,366	03/26/1998	Berg et al.	
JMD	34	5,795,823	08/18/1998	Avanzino et al.	
JMD	35	5,861,328	01/19/1999	Tehrani et al.	
JMD	36	5,926,394	07/20/1999	Nguyen et al.	
JMD	37	5,956,267	09/21/1999	Hurst et al.	
JMD	38	5,982,658	11/09/1999	Berg et al.	
JMD	39	6,028,786	02/22/2000	Nishimura	
JMD	40	6,048,739	04/11/2000	Hurst et al.	
JMD	41	6,136,705	10/24/2000	Blair	
JMD	42	6,153,443	11/28/2000	Durlam et al.	
JMD	43	6,174,737	01/16/2001	Durlam et al.	
JMD	44	6,211,559	04/03/2001	Zhu et al.	
JMD	45	6,218,302	04/17/2001	Braeckelmann et al.	
JMD	46	6,338,899	01/15/2002	Fukuzawa et al.	
JMD	47	6,358,756	03/19/2002	Sandhu et al.	
JMD	48	6,379,978	04/30/2002	Goebel et al.	
JMD	49	6,391,658	05/21/2002	Gates et al.	
JMD	50	6,392,922	05/21/2002	Liu et al.	
JMD	51	6,440,753	08/27/2002	Ning et al.	
JMD	52	6,485,989	11/26/2002	Signorini	
JMD	53	6,627,913	09/30/03	Chen	
JMD	54	US 2002/0041514 A1	04/11/2002	Scheler et al.	

## FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T <sup>1</sup>
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Examiner Signature	Date Considered 3/26/05
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<i>JMS</i>	55	DE 198 36 567 A1	02/24/2000	Schwarz		
<i>JMS</i>	56	EP 0 271 017 A2	06/15/1988	Schuetz		
<i>JMS</i>	57	EP 0 450 911 A2	10/09/1991	Daughton et al.		
<i>JMS</i>	58	EP 0 776 011 A2	05/28/1997	Chen et al.		
<i>JMS</i>	59	JP 2000-30222	01/ /2000	Seyama		
<i>JMS</i>	60	WO 98/20496	05/14/1998	Daughton et al.		
<i>JMS</i>	61	WO 00/19440	04/06/2000	Weber et al.		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>1</sup>
<i>JMS</i>	62	Honeywell Brochure entitled Pohm et al., "The Architecture of a High Performance Mass Store with GMR Memory Cells," <u>Nonvolatile Electronics</u> , pp. 1-3.	
<i>JMS</i>	63	Pohm et al., "Experimental and Analytical Properties of 0.2 Micron Wide, Multi-Layer, GmR, Memory Elements," <u>IEEE Transactions on Magnetics</u> , Vol. 32, No. 5, September 1996, pp. 4645-4647.	
<i>JMS</i>	64	Prinz, Gary, "Magnetoelectronics," <u>Science</u> , Vol. 282, November 27, 1998, pp. 1660-1663.	
<i>JMS</i>	65	Wang, Zhi G. et al., "Feasibility of Ultra-Dense Spin-Tunneling Random Access Memory," <u>IEEE Transactions on Magnetics</u> , Vol. 33, No. 6, November 1997, pp. 4498-4512.	
<i>JMS</i>	66	Razavi et al., "Design Techniques for High-Speed, High-Resolution Comparators," <u>IEEE Journal of Solid State Circuit</u> , Vol. 27, No. 12, December 1992	

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